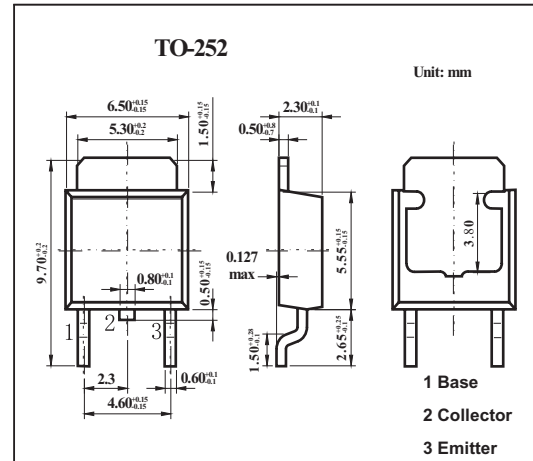


Silicon PNP Epitaxial

2SB1407S

■ Features

- Low frequency power amplifier.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	-35	V
Collector to emitter voltage	V _{CEO}	-35	V
Emitter to base voltage	V _{EB0}	-5	V
Collector current	I _C	-2.5	A
Peak collector current	I _{CP}	-3	A
Collector power dissipation	P _C	18	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -1 mA, I _E = 0	-35			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -10 mA, R _{BE} = ∞	-35			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -1 mA, I _C = 0	-5			V
Collector cutoff current	I _{CBO}	V _{CB} = -35 V, I _E = 0			-20	μA
DC current transfer ratio	h _{FE}	V _{CE} = -2 V, I _C = -0.5 A	60		320	
		V _{CE} = -2 V, I _C = -1.5 A	20			
Base to emitter voltage	V _{BE}	V _{CE} = -2 V, I _C = -1.5 A			-1.5	V
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -2 A, I _B = -0.2 A			-1.0	V

■ hFE Classification

Rank	B	C	D
hFE	60~120	100~200	160~320